

**Gate resistor installed
Dual N-channel MOSFET**

**KFCAB21490L
Data Sheet**

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source On-state resistance: RSS (on) typ. = 2.2 mΩ (VGS = 3.8 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: 7F

4. PACKAGING

Embossed type (Thermo-compression sealing): 10,000 pcs / reel (standard)

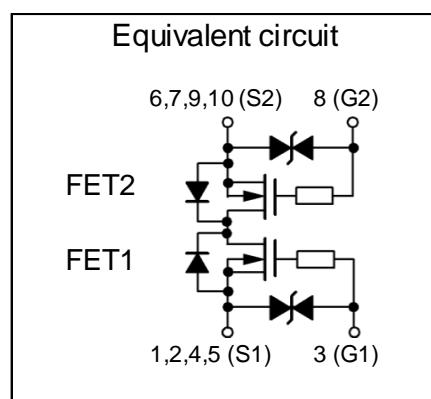
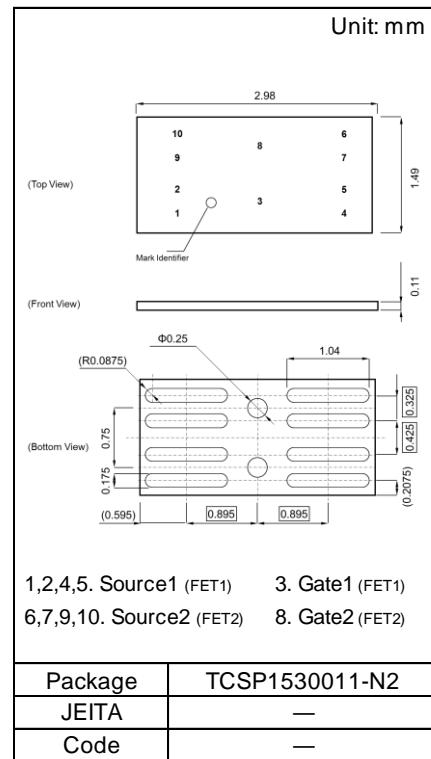
5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	±8	V
Source Current	DC ^{*1}	IS1	13.5
	DC ^{*2}	IS2	29
	Pulsed ^{*3}	ISp	135
Total Power Dissipation	DC ^{*1}	PD1	0.54
	DC ^{*2}	PD2	3.5
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note ^{*1} Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm)
using the minimum recommended pad size (36 µm Copper).

^{*2} Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).

^{*3} t = 10 µs, Duty Cycle ≤ 1 %



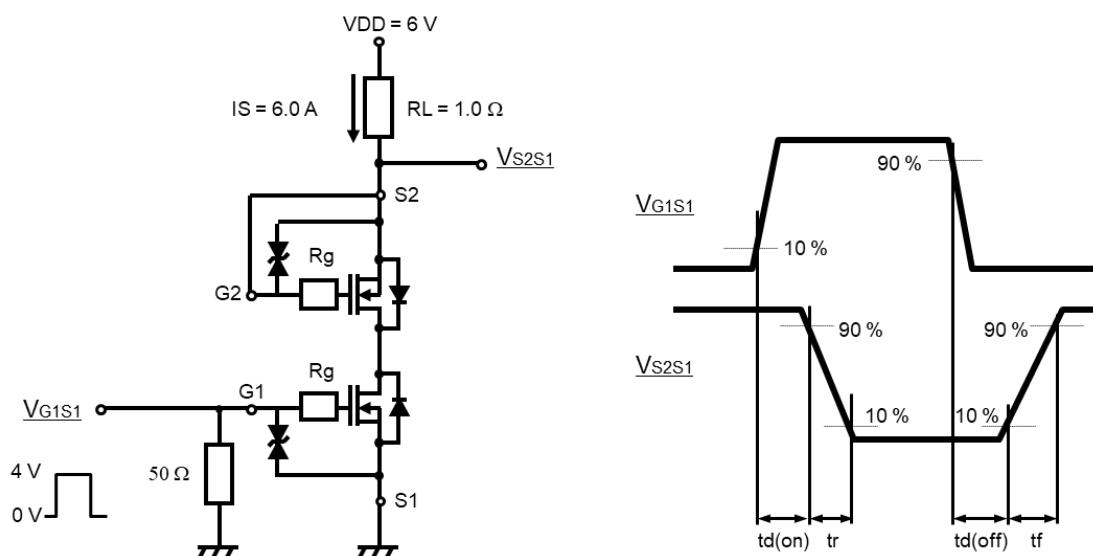
6. ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	V _{SSS}	$I_S = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	12			V
Zero Gate Voltage Source Current	I _{SSS}	$V_{SS} = 12 \text{ V}, V_{GS} = 0 \text{ V}$			1.0	μA
Gate-source Leakage Current	I _{GSS1}	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$			± 10	μA
	I _{GSS2}	$V_{GS} = \pm 5 \text{ V}, V_{SS} = 0 \text{ V}$			± 1.0	
Gate-source Threshold Voltage	V _{th}	$I_S = 1.11 \text{ mA}, V_{SS} = 10 \text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	R _{S(on)1}	$I_S = 6.0 \text{ A}, V_{GS} = 4.5 \text{ V}$	1.55	2.10	2.75	$\text{m}\Omega$
	R _{S(on)2}	$I_S = 6.0 \text{ A}, V_{GS} = 3.8 \text{ V}$	1.60	2.20	2.85	
	R _{S(on)3}	$I_S = 6.0 \text{ A}, V_{GS} = 3.1 \text{ V}$	1.65	2.40	3.95	
	R _{S(on)4}	$I_S = 6.0 \text{ A}, V_{GS} = 2.5 \text{ V}$	1.90	3.10	6.10	
Body Diode Forward Voltage	V _{F(s-s)}	$I_F = 6.0 \text{ A}, V_{GS} = 0 \text{ V}$		0.6	1.2	V
Input Capacitance ^{*1}	C _{iss}	$V_{SS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$		3570		pF
Output Capacitance ^{*1}	C _{oss}			460		
Reverse Transfer Capacitance ^{*1}	C _{rss}			410		
Turn-on Delay Time ^{*1,*2}	t _{d(on)}			0.7		μs
Rise Time ^{*1,*2}	t _r	$I_S = 6.0 \text{ A}$		1.5		
Turn-off Delay Time ^{*1,*2}	t _{d(off)}	$V_{DD} = 6 \text{ V}, V_{GS} = 4 \text{ to } 0 \text{ V}$		6.7		μs
Fall Time ^{*1,*2}	t _f	$I_S = 6.0 \text{ A}$		4.1		
Total Gate Charge ^{*1}	Q _g	$V_{DD} = 6 \text{ V}$		25		nC
Gate-source Charge ^{*1}	Q _{gs}	$V_{GS} = 0 \text{ to } 4 \text{ V}$		12		
Gate-drain Charge ^{*1}	Q _{gd}	$I_S = 6.0 \text{ A}$		6		

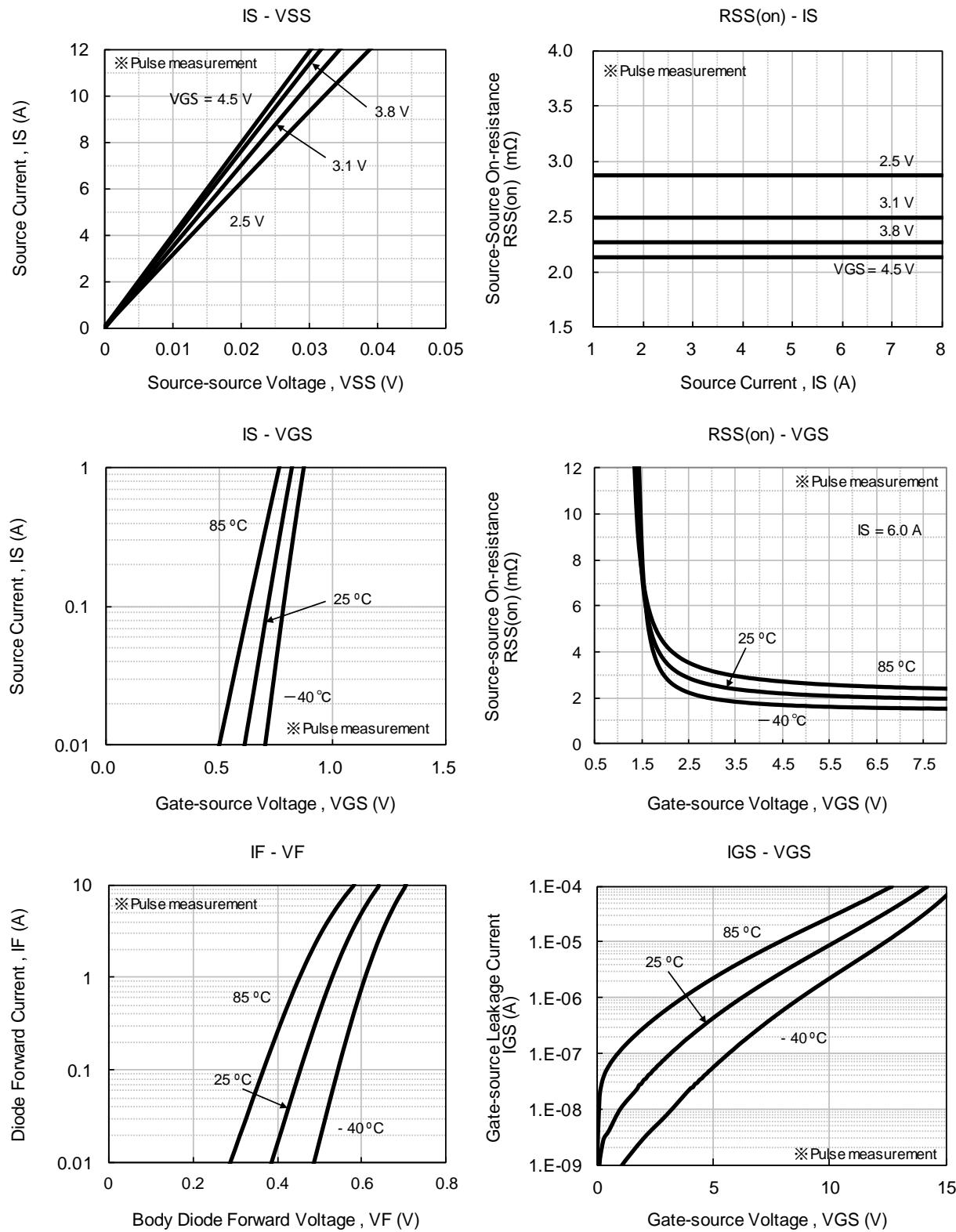
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

^{*1} Guaranteed by design, not subject to production testing

^{*2} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

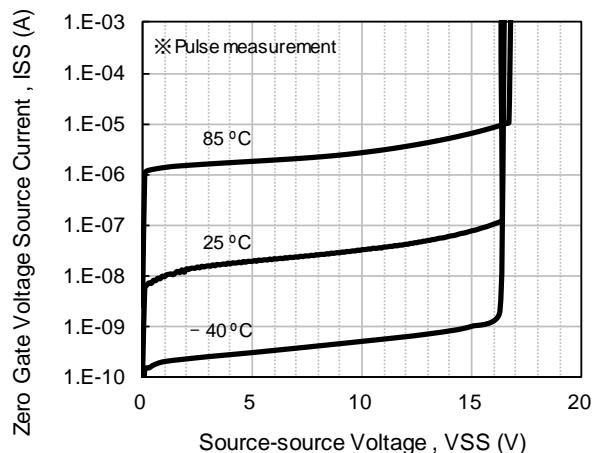


7. TECHNICAL DATA (Reference)

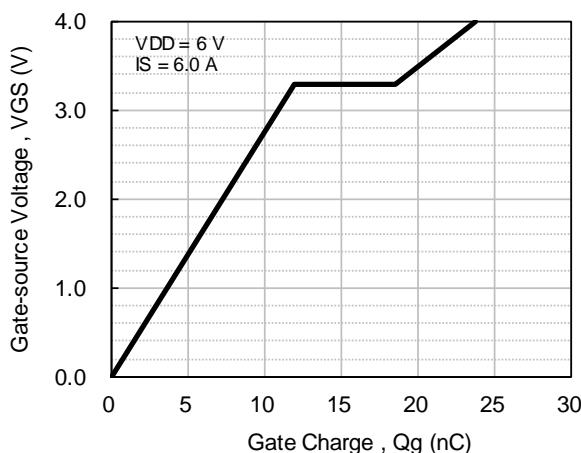


TECHNICAL DATA (Reference)

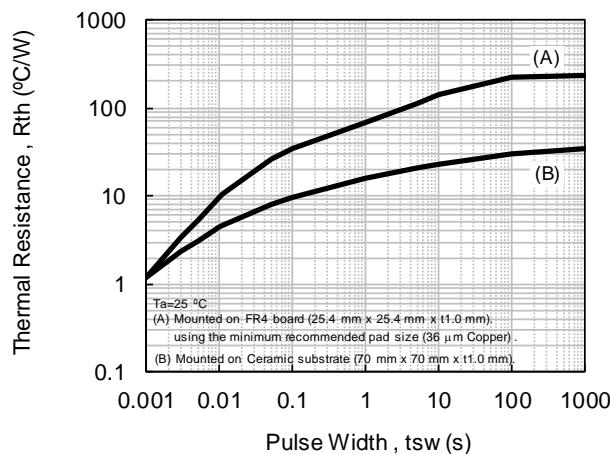
ISS - VSS



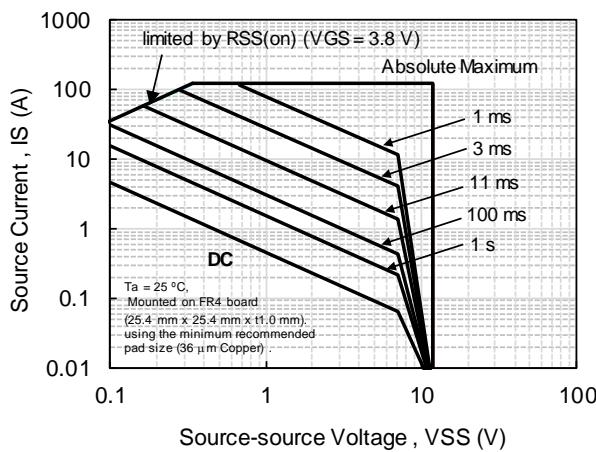
Dynamic Input / Output Characteristics



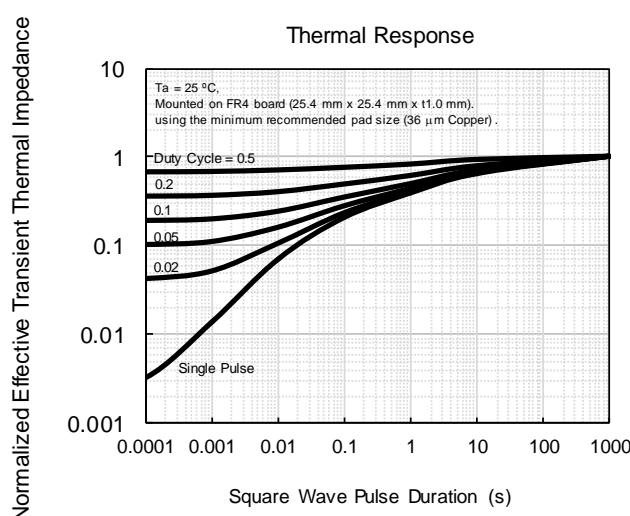
Rth - tsw



Safe Operating Area

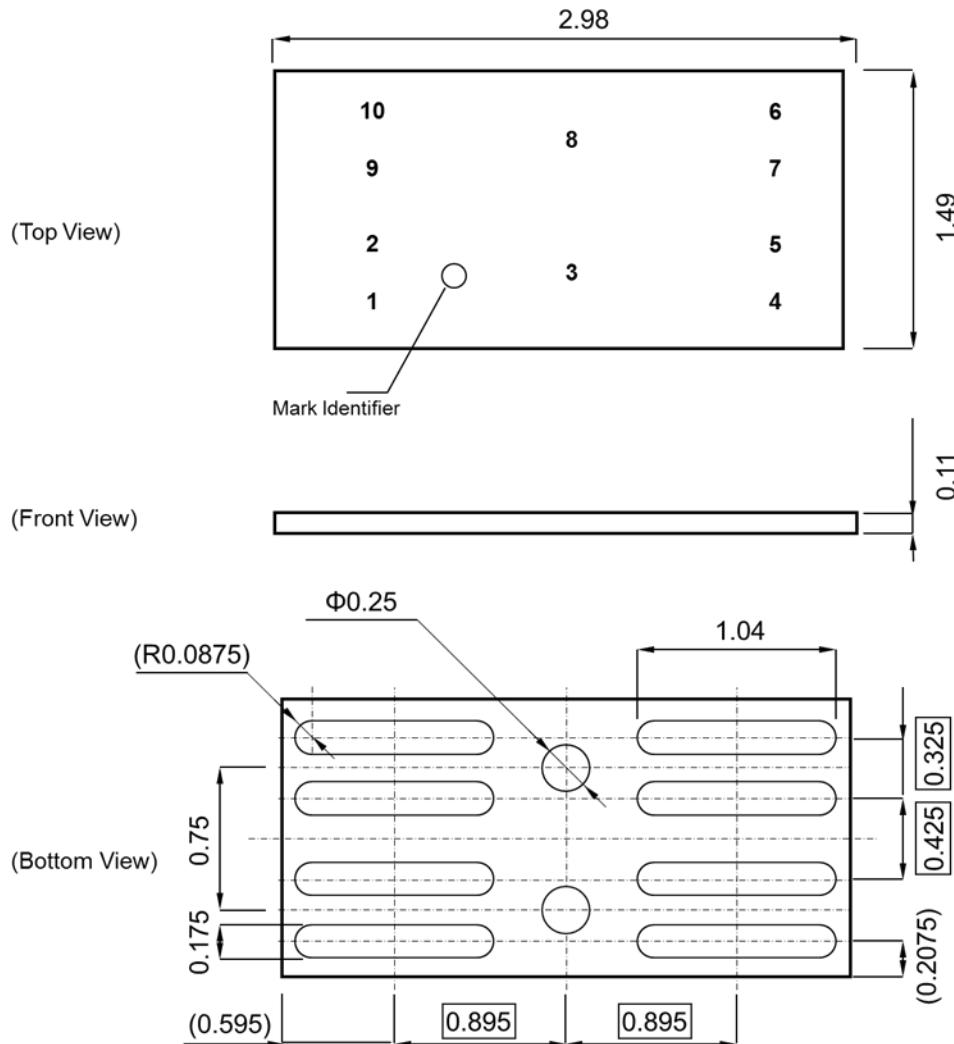


Thermal Response



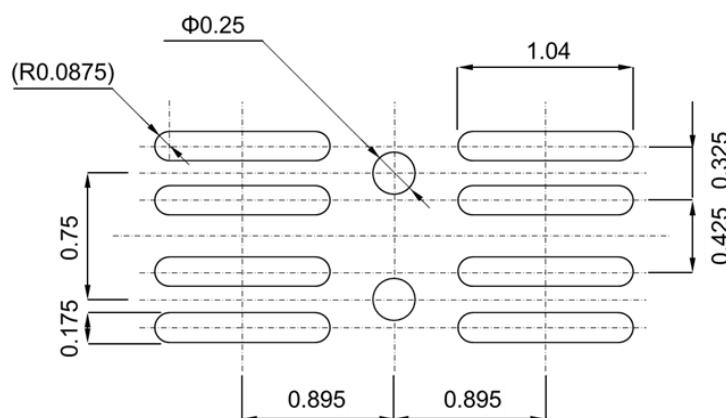
8. OUTLINE

Unit : mm



9. LAND PATTERN (Reference)

Unit : mm



10. REVISION HISTORY

Date	Revision	Description
2021.2.8	1.00	1. initially issued.

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